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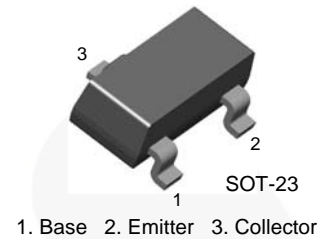


October 2014

KST2222A NPN Epitaxial Silicon Transistor

Features

- General-Purpose Transistor



Ordering Information

Part Number	Marking	Package	Packing Method
KST2222AMTF	1P	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	600	mA
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics⁽¹⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	350	mW
	Derate Above 25°C	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	75		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10\ \text{mA}, I_B = 0$	40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\ \mu\text{A}, I_C = 0$	6		V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 60\ \text{V}, I_E = 0$		0.01	μA
h_{FE}	DC Current Gain ⁽²⁾	$V_{CE} = 10\ \text{V}, I_C = 0.1\ \text{mA}$	35		
		$V_{CE} = 10\ \text{V}, I_C = 1\ \text{mA}$	50		
		$V_{CE} = 10\ \text{V}, I_C = 10\ \text{mA}$	75		
		$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}$	100	300	
		$V_{CE} = 10\ \text{V}, I_C = 500\ \text{mA}$	40		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ⁽²⁾	$I_C = 150\ \text{mA}, I_B = 15\ \text{mA}$		0.3	V
		$I_C = 500\ \text{mA}, I_B = 50\ \text{mA}$		1.0	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ⁽²⁾	$I_C = 150\ \text{mA}, I_B = 15\ \text{mA}$	0.6	1.2	V
		$I_C = 500\ \text{mA}, I_B = 50\ \text{mA}$		2.0	
f_T	Current Gain Bandwidth Product	$I_C = 20\ \text{mA}, V_{CE} = 20\ \text{V}, f = 100\ \text{MHz}$	300		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		8	pF
NF	Noise Figure	$I_C = 100\ \mu\text{A}, V_{CE} = 10\ \text{V}, R_S = 1\ \text{k}\Omega, f = 1\ \text{MHz}$		4	dB
t_{ON}	Turn-On Time	$V_{CC} = 30\ \text{V}, I_C = 150\ \text{mA}, V_{BE} = 0.5\ \text{V}, I_{B1} = 15\ \text{mA}$		35	ns
t_{OFF}	Turn-Off Time	$V_{CC} = 30\ \text{V}, I_C = 150\ \text{mA}, I_{B1} = I_{B2} = 15\ \text{mA}$		285	ns

Note:

2. Pulse test: Pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

Typical Performance Characteristics

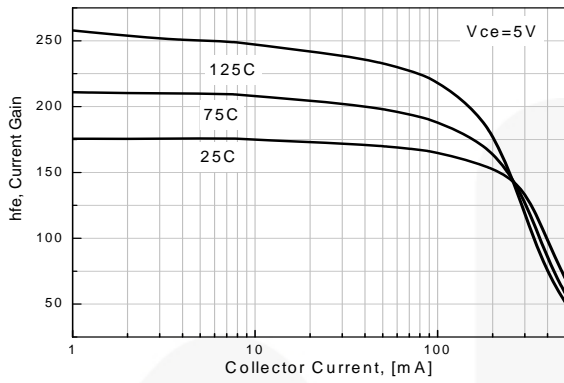


Figure 1. DC Current Gain

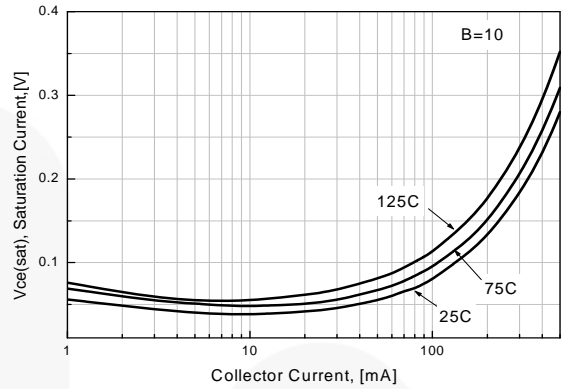


Figure 2. Collector-Emitter Saturation Voltage

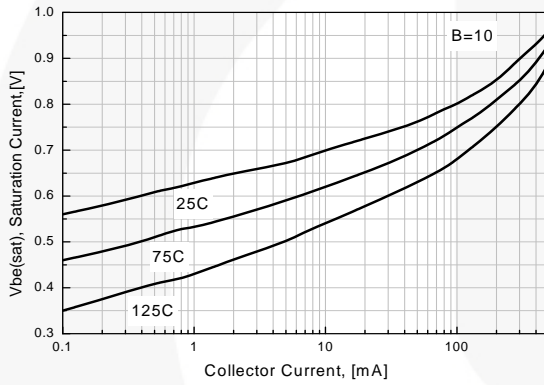


Figure 3. Base-Emitter Saturation Voltage

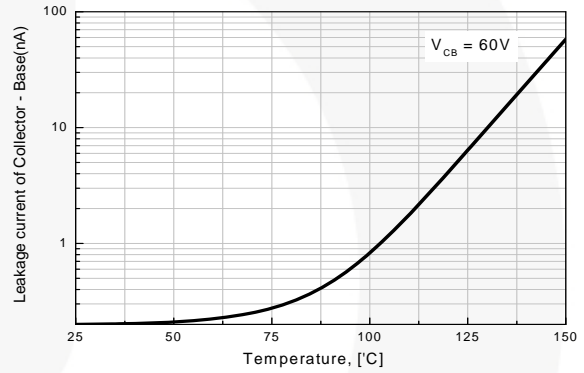


Figure 4. Collector-Base Leakage Current

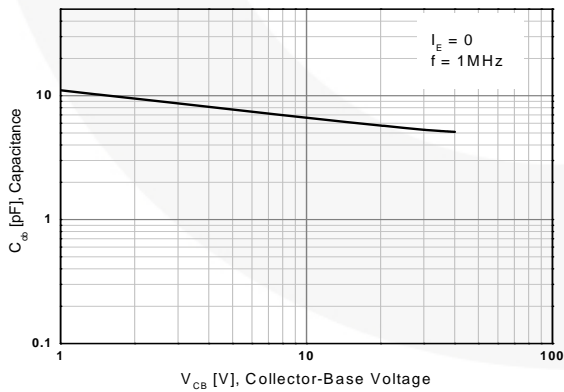


Figure 5. Output Capacitance

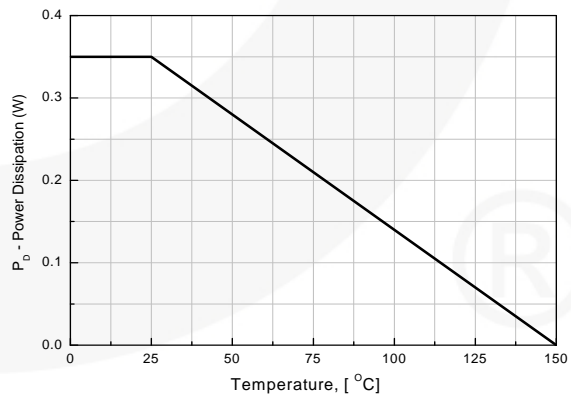
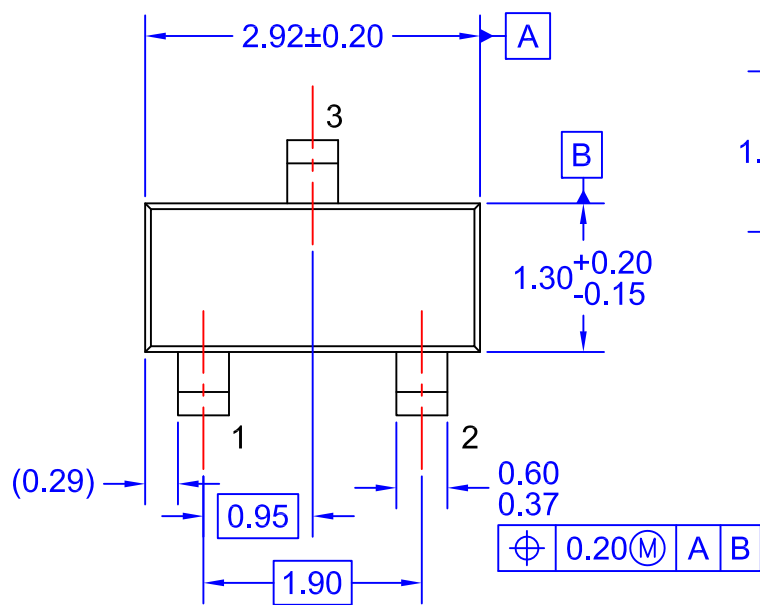


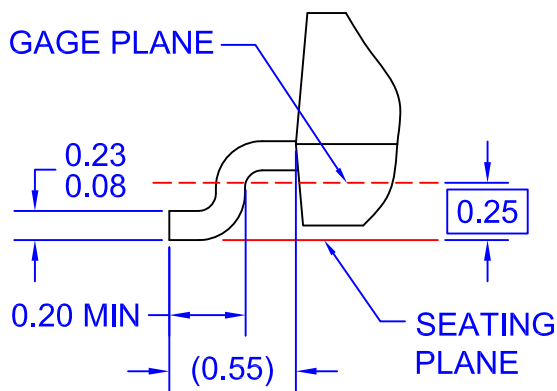
Figure 6. Power Dissipation vs. Ambient Temperature



LAND PATTERN
RECOMMENDATION



SEE DETAIL A



DETAIL A
SCALE: 2X

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